

SCDS211C - AUGUST 2006 - REVISED DECEMBER 2009

# $0.75-\Omega$ SPDT ANALOG SWITCH WITH INPUT LOGIC TRANSLATION

Check for Samples: TS5A6542

## FEATURES

- Specified Break-Before-Make Switching
- Low ON-State Resistance (0.75 Ω Max)
- Control Inputs Referenced to V<sub>IO</sub>
- Low Charge Injection
- Excellent ON-State Resistance Matching
- Low Total Harmonic Distortion (THD)
- 2.25-V to 5.5-V Power Supply (V<sub>+</sub>)
- 1.65-V to 1.95-V Logic Supply (V<sub>ι0</sub>)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
  - 4000-V Human-Body Model (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)
  - 400-V Machine Model (A115-A)

## **DESCRIPTION/ORDERING INFORMATION**

• COM Port to GND

- 8000-V Human-Body Model (A114-B, Class II)
- ±15-kV Contact Discharge (IEC 61000-4-2)

## **APPLICATIONS**

- Cell Phones
- PDAs
- Portable Instrumentation

### YZP PACKAGE (BOTTOM VIEW)

VIO	D1)4	5 D2	V+
NC GND	C1 3	6 😋	IN
GND	B1 2	7 B2	СОМ
NO	(Å1) 1	8 A2	GND
	_		

The TS5A6542 is a single-pole double-throw (SPDT) analog switch that is designed to operate from 2.25 V to 5.5 V. The device offers a low ON-state resistance with an excellent channel-to-channel ON-state resistance matching, and the break-before-make feature to prevent signal distorion during the transferring of a signal from one path to another. The device has excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

The TS5A6542 has a separate logic supply pin ( $V_{IO}$ ) that is characterized to operate from 1.65 V to 1.95 V.  $V_{IO}$  powers the control circuitry, which allows the TS5A6542 to be controlled by 1.8-V signals.

٦	T <sub>A</sub>	PACKAGE <sup>(2)</sup>		ORDERABLE PART NUMBER	TOP-SIDE MARKING <sup>(3)</sup>
-40°C		NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Tape and reel	TS5A6542YZPR	JH7

#### Table 1. ORDERING INFORMATION<sup>(1)</sup>

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

(3) YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the wafer fab/assembly site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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AUTERIUTIOU
2:1 Multiplexer/Demultiplexer (1 × SPDT)
1
0.75 Ω max
0.1 Ω max
0.1 Ω max
25 ns/20 ns
15 pC
43 MHz
–63 dB at 1 MHz
–63 dB at 1 MHz
0.004%
20 nA
8-pin WCSP

## SUMMARY OF CHARACTERISTICS<sup>(1)</sup>

(1)  $V_+ = 5 V, T_A = 25^{\circ}C$ 

### **FUNCTION TABLE**

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
Н	OFF	ON

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#### ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup> <sup>(2)</sup>

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V+ V <sub>IO</sub>	Supply voltage range <sup>(3)</sup>		-0.5	6.5	V
V <sub>NC</sub> V <sub>NO</sub> V <sub>COM</sub>	Analog voltage range <sup>(3)</sup> <sup>(4)</sup> <sup>(5)</sup>		-0.5	V <sub>+</sub> + 0.5	v
I <sub>I/OK</sub>	Analog port diode current <sup>(6)</sup>	$V_{NO}$ , $V_{COM}$ < 0 or $V_{NO}$ , $V_{COM}$ > $V_{+}$	-50	50	mA
I <sub>NC</sub>	On-state switch current		-450	450	
I <sub>NO</sub> I <sub>COM</sub>	On-state peak switch current <sup>(7)</sup>	$V_{NO,} V_{COM} = 0 \text{ to } V_+$	-700	700	mA
VI	Digital input voltage range <sup>(3) (4)</sup>		-0.5	6.5	V
I <sub>IK</sub>	Digital input clamp current	V <sub>1</sub> < 0	-50		mA
I <sub>+</sub> I <sub>GND</sub>	Continuous current through $V_+$ or GNE	)	-100	100	mA
T <sub>stg</sub>	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(3) All voltages are with respect to ground, unless otherwise specified.

(4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

(5) This value is limited to 5.5 V maximum.

(6) Requires clamp diodes on analog port to  $V_+$ 

(7) Pulse at 1-ms duration < 10% duty cycle

## THERMAL IMPEDANCE RATINGS

			UNIT	1
$\theta_{JA}$ Package thermal impedance <sup>(1)</sup>	YZP package	102	°C/W	

(1) The package thermal impedance is calculated in accordance with JESD 51-7.

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## ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY<sup>(1)</sup>

 $V_{+}$  = 4.5 V to 5.5 V,  $V_{IO}$  = 1.65 V to 1.95 V,  $T_{A}$  =  $-40^{\circ}C$  to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	S 1	Γ <sub>A</sub>	V+	MIN	TYP	MAX	UNIT
Analog Switch	·	·				·			
Analog signal range	V <sub>COM</sub> , V <sub>NO</sub>					0		V+	V
ON-state resistance	r	$V_{NO}$ or $V_{NC}$ = 2.5 V, Switch 0	JIN,	5°C	4.5 V		0.5	0.75	Ω
ON-State resistance	r <sub>on</sub>	$I_{COM} = -100 \text{ mA},$ See Fig	ure 14 F	ull	4.5 V			0.8	32
ON-state resistance	٨٢	$V_{NO}$ or $V_{NC}$ = 2.5 V, Switch 0	DN, 25	5°C	4.5 V		0.05	0.1	Ω
match between channels	∆r <sub>on</sub>	$I_{COM} = -100 \text{ mA},$ See Fig	ure 14 F	ull	4.5 V			0.1	Ω
ON-state resistance	-	$\begin{array}{ll} 0 \leq (V_{NO} \text{ or } V_{NC}) \leq \\ V_{+}, \\ I_{COM} = -100 \text{ mA}, \end{array} \qquad \begin{array}{l} \text{Switch } 0 \\ \text{See Fig} \end{array}$		5°C	4.5 V		0.1		Ω
flatness	r <sub>on(flat)</sub>	$V_{NO} \text{ or } V_{NC} = 1 \text{ V},$ Switch O	ON. 25	5°C	4.5 V		0.1	0.25	12
		1.5 V, 2.5 V, Switch C $I_{COM} = -100 \text{ mA},$ See Fig		ull				0.25	
		V <sub>NO</sub> = 1 V, 4.5 V,	25	5°C		-20	2	20	
NO, NC OFF leakage current	$I_{NO(OFF)}, I_{NC}$ $(OFF)$ $V_{NC} = 0 p$ $0 r$ $V_{NC} = 1 V$ $V_{COM} = 4$	$ \begin{array}{l} V_{COM}^{c} = 4.5 \ V, \ 1 \ V, \\ V_{NC} = Open, \\ or \\ V_{NC} = 1 \ V, \ 4.5 \ V, \\ V_{COM} = 4.5 \ V, \ 1 \ V, \\ V_{NO} = Open, \end{array} \\ \begin{array}{l} \text{Switch C} \\ \text{See Fig} \\ \end{array} $	45	ull	5.5 V	-100		100	nA
		$V_{NO} = 1 V, 4.5 V,$	25	5°C		-20	2	20	[
NC, NO ON leakage current	I <sub>NO(ON)</sub>	$ \begin{array}{l} V_{COM},  V_{NC} = Open, \\ or \\ V_{NC} = 1  V,  4.5  V, \\ V_{COM},  V_{NO} = Open, \end{array} \\ \begin{array}{l} \text{Switch C} \\ \text{See Fig} \end{array} $	10	ull	5.5 V	-200		200	nA
		$V_{COM} = 1 V, 4.5 V,$	25	5°C		-20	2	20	
COM ON leakage current	I <sub>COM(ON)</sub>	$\begin{array}{ll} V_{NO} \text{ and } V_{NC} = \\ Open, & See \ \mbox{Fig} \\ or & \\ V_{COM} = 1 \ \mbox{V}, \ 4.5 \ \mbox{V}, \\ V_{NO} \ \mbox{or} \ \ \mbox{V}_{NC} = Open, \end{array}$	ure 16 F	ull	5.5 V	-200		200	nA
Digital Control Input	(IN) <sup>(2)</sup>								
Input logic high	V <sub>IH</sub>	V <sub>IO</sub> = 1.65 V to 1.95 V	F	ull		0.65 × V <sub>IO</sub>		V <sub>IO</sub>	V
Input logic low	V <sub>IL</sub>	V <sub>IO</sub> = 1.65 V to 1.95 V	F	ull		0		0.35 × V <sub>IO</sub>	V
Input leakage current $I_{IH}$ , $I_{IL}$ $V_I = V_{IO} \text{ or } 0$ $\frac{25^{\circ}\text{C}}{\text{Full}}$ 5.5	5.5 V	-2		2	nA				
	$I_{\rm IH}, I_{\rm IL}$		F	ull	0.0 V	-20		20	ПA

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V<sub>IO</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

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## ELECTRICAL CHARACTERISTICS FOR 5-V SUPPLY <sup>(1)</sup> (continued)

V<sub>+</sub> = 4.5 V to 5.5 V, V<sub>IO</sub> = 1.65 V to 1.95 V, T<sub>A</sub> =  $-40^{\circ}$ C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CO	ONDITIONS	T <sub>A</sub>	۷.	MIN	TYP	MAX	UNIT
Dynamic				r	l				
Turn-on time	t <sub>ON</sub>	$V_{COM} = V_+,$	$C_L = 35 \text{ pF},$	25°C	5 V	1	12.5	25	ns
		$R_L = 50 \Omega,$	See Figure 18	Full	4.5 V			30	
Turn-off time	t <sub>OFF</sub>	$V_{COM} = V_+,$	C <sub>L</sub> = 35 pF,	25°C	5 V	1	9.5	20	ns
	OFF	$R_L = 50 \Omega$ ,	See Figure 18	Full	4.5 V			25	110
Break-before-make	+	$V_{NC} = V_{NO} = V_{+}/2,$	C <sub>L</sub> = 35 pF,	25°C	5 V	1	5	10	20
time	t <sub>BBM</sub>	$R_L = 50 \Omega$ ,	See Figure 19	Full	4.5 V	1		12	ns
Charge injection	Q <sub>C</sub>	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C <sub>L</sub> = 1 nF, See Figure 23	25°C	5 V		15		рС
NO OFF capacitance	C <sub>NO(OFF)</sub>	$V_{NO} = V_{+} \text{ or GND},$ Switch OFF,	See Figure 17	25°C	5 V		37		pF
NC, NO ON capacitance	C <sub>NC(ON)</sub> , C <sub>NO(ON)</sub>	$V_{NC}$ or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 17	25°C	5 V		130		pF
COM ON capacitance	C <sub>COM(ON)</sub>	$V_{COM} = V_+ \text{ or GND},$ Switch ON,	See Figure 17	25°C	5 V		130		pF
Digital input capacitance	Cl	$V_{I} = V_{IO} \text{ or } GND,$	See Figure 17	25°C	5 V		6.5		pF
Bandwidth	BW	$R_L = 50 \Omega$ , Switch ON,	See Figure 20	25°C	5 V		43		MHz
OFF isolation	O <sub>ISO</sub>	$R_L = 50 \Omega,$ f = 1 MHz,	See Figure 21	25°C	5 V		-63		dB
Crosstalk	X <sub>TALK</sub>	$R_L = 50 \Omega,$ f = 1 MHz,	See Figure 22	25°C	5 V		-63		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 24	25°C	5 V		0.00 4		%
Supply									
Positive supply				25°C	<b>D</b>		5.5	100	
current	I+	$V_I = V_{IO}$ or GND		Full	5.5 V			750	nA

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## ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY<sup>(1)</sup>

 $V_+$  = 3 V to 3.6 V,  $V_{IO}$  = 1.65 V to 1.95 V,  $T_A$  = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDIT	IONS	T <sub>A</sub>	V <sub>+</sub>	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V <sub>COM</sub> , V <sub>NO</sub>					0		V+	V
ON-state resistance	r <sub>on</sub>	$V_{NO}$ or $V_{NC} = 2 V$ , $I_{COM} = -100 \text{ mA}$ ,	Switch ON, See Figure 14	25°C Full	3 V		0.75	0.9 1.2	Ω
ON-state resistance match between	Δr <sub>on</sub>	$V_{NO} \text{ or } V_{NC} = 2 \text{ V}, 0.8 \text{ V},$	Switch ON,	25°C	3 V		0.1	0.15	Ω
channels	Δι <sub>on</sub>	$I_{COM} = -100 \text{ mA},$	See Figure 14	Full	5.0			0.15	12
ON-state resistance		$\begin{array}{l} 0 \leq (V_{\text{NO}} \text{ or } V_{\text{NC}}) \leq V_{+}, \\ I_{\text{COM}} = -100 \text{ mA}, \end{array}$	Switch ON, See Figure 14	25°C	- N		0.2		
flatness	r <sub>on(flat)</sub>	$V_{NO}$ or $V_{NC}$ = 0.8 V, 2 V,		25°C	3 V		0.1	0.3	Ω
		I <sub>COM</sub> = -100 mA,	See Figure 14	Full				0.3	
		V <sub>NO</sub> = 1 V, 3 V, V <sub>COM</sub> = 3 V, 1 V,		25°C	-	-20	2	20	nA
NO, NC OFF leakage current	I <sub>NO(OFF)</sub> , I <sub>NC</sub> (OFF)		Switch OFF, See Figure 15	Full	3.6 V	-50		50	
		V <sub>NO</sub> = 1 V, 3 V,		25°C		-10	2	10	
NC, NO ON leakage current	I <sub>NO(ON)</sub>	$\label{eq:VNC} \begin{array}{l} V_{NC} \text{ and } V_{COM} = \text{Open}, \\ \text{or} \\ V_{NC} = 1 \text{ V}, \text{ 3 V}, \\ V_{NO} \text{ and } V_{COM} = \text{Open}, \end{array}$	Switch ON, See Figure 16	Full	3.6 V	-30		30	nA
		$V_{COM} = 1 V,$		25°C		-10	2	10	
COM ON leakage current	I <sub>COM(ON)</sub>	$\label{eq:VNC} \begin{array}{l} V_{NO} \text{ and } V_{NC} = Open, \\ \text{or} \\ V_{COM} = 3 \ \text{V}, \\ V_{NO} \text{ and } V_{NC} = Open, \end{array}$	See Figure 16	Full	3.6 V	-30		30	nA
Digital Control Input	(IN) <sup>(2)</sup>								
Input logic high	V <sub>IH</sub>	V <sub>IO</sub> = 1.65 V to 1.95 V		Full		0.65 × V <sub>IO</sub>		V <sub>IO</sub>	V
Input logic low	V <sub>IL</sub>	V <sub>IO</sub> = 1.65 V to 1.95 V		Full		0		0.35 × V <sub>IO</sub>	V
Input leakage current	I <sub>IH</sub> , I <sub>IL</sub>	$V_{I} = V_{IO} \text{ or } 0$		25°C	3.6 V	-2		2	nA
input loanage ourient	'IH', 'IL			Full	0.0 V	-20		20	11/5

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

 (2) All unused digital inputs of the device must be held at V<sub>IO</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

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## ELECTRICAL CHARACTERISTICS FOR 3.3-V SUPPLY <sup>(1)</sup> (continued)

 $V_{+} = 3 \text{ V}$  to 3.6 V,  $V_{IO} = 1.65 \text{ V}$  to 1.95 V,  $T_{A} = -40^{\circ}\text{C}$  to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CON	DITIONS	TA	۷,	MIN	TYP	MAX	UNIT
Dynamic	I		<b>I</b>		1				
Turn-on time	t <sub>ON</sub>	$V_{COM} = V_+,$ $R_1 = 50 \Omega,$	C <sub>L</sub> = 35 pF, See Figure 18	25°C Full	3.3 V 3 V	5	15	30 35	ns
		$V_{COM} = V_+,$	C <sub>L</sub> = 35 pF,	25°C	3.3 V	1	9	20	
Turn-off time	t <sub>OFF</sub>	$R_L = 50 \Omega,$	See Figure 18	Full	3 V	1		25	ns
Break-before-make time	t <sub>BBM</sub>	$V_{\text{NC}} = V_{\text{NO}} = V_{+}/2,$ R <sub>L</sub> = 50 Ω,	C <sub>L</sub> = 35 pF, See Figure 19	25°C Full	3.3 V 3 V	1	8	13 15	ns
Charge injection	Q <sub>C</sub>	$V_{\text{GEN}} = 0,$ $R_{\text{GEN}} = 0,$	C <sub>L</sub> = 1 nF, See Figure 23	25°C	3.3V		6.5		рС
NO OFF capacitance	C <sub>NO(OFF)</sub>	$V_{NO} = V_{+} \text{ or GND},$ Switch OFF,	See Figure 17	25°C	3.3 V		38		pF
NC, NO ON capacitance	C <sub>NC(ON)</sub> , C <sub>NO(ON)</sub>	$V_{NC}$ or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 17	25°C	3.3 V		133		pF
COM ON capacitance	C <sub>COM(ON)</sub>	$V_{COM} = V_+ \text{ or GND},$ Switch ON,	See Figure 17	25°C	3.3 V		133		pF
Digital input capacitance	CI	$V_I = V_{IO}$ or GND,	See Figure 17	25°C	3.3 V		6.5		pF
Bandwidth	BW	$R_L = 50 \Omega$ , Switch ON,	See Figure 20	25°C	3.3 V		42		MHz
OFF isolation	O <sub>ISO</sub>	$R_L = 50 \Omega,$ f = 1 MHz,	See Figure 21	25°C	3.3 V		-63		dB
Crosstalk	X <sub>TALK</sub>	$R_L = 50 \Omega,$ f = 1 MHz,	See Figure 22	25°C	3.3 V		-63		dB
Total harmonic distortion	THD	$\begin{aligned} R_L &= 600 \ \Omega, \\ C_L &= 50 \ pF, \end{aligned}$	f = 20 Hz to 20 kHz, See Figure 24	25°C	3.3 V		0.00 4		%
Supply									
Positive supply		$V_{I} = V_{IO} \text{ or } GND$	25°C	261/		10	50	n۸	
current	I+			Full	3.6 V			300	) nA

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## **ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY**<sup>(1)</sup>

 $V_+$  = 2.25 V to 2.75 V,  $V_{IO}$  = 1.65 V to 1.95 V,  $T_A$  = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDIT	IONS	T <sub>A</sub>	۷.	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V <sub>COM</sub> , V <sub>NO</sub>					0		V+	V
ON-state resistance	r <sub>on</sub>	$V_{NO}$ or $V_{NC}$ = 1.8 V, $I_{COM}$ = -100 mA,	Switch ON, See Figure 14	25°C Full	2.25 V		1	1.3 1.6	Ω
ON-state resistance match between channels	Δr <sub>on</sub>	$V_{NO} \text{ or } V_{NC} = 1.8 \text{ V},$ 0.8 V, $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 14	25°C Full	2.25 V		0.15	0.2 0.2	Ω
ON-state resistance		$0 \le (V_{NO} \text{ or } V_{NC}) \le V_+,$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 14	25°C			0.5		
flatness	r <sub>on(flat)</sub>	$V_{\rm NO}$ or $V_{\rm NC} = 0.8$ V, 1 V,	Switch ON,	25°C	2.25 V		0.25	0.5	Ω
		1.8 V, I <sub>COM</sub> = -100 mA,	See Figure 14	Full				0.6	
		V <sub>NO</sub> = 0.5 V, 2.2 V,		25°C		-20	2	20	
NO, NC OFF leakage current	I <sub>NO(OFF)</sub> , I <sub>NC</sub> (OFF)	$ \begin{array}{l} V_{COM} = 2.2 \ V, \ 0.5 \ V, \\ V_{NC} = Open, \\ or \\ V_{NC} = 0.5 \ V, \ 2.2 \ V, \\ V_{COM} = 2.2 \ V, \ 0.5 \ V, \\ V_{NO} = Open, \end{array} $	Switch OFF, See Figure 15	Full	2.75 V	-50 50	50	nA	
		$V_{\rm NO} = 0.5  \rm V,  2.2  \rm V,$		25°C		-10	2	10	
NC, NO ON leakage current	I <sub>NO(ON)</sub>	$ \begin{array}{l} V_{NC} \text{ and } V_{COM} = \text{Open}, \\ \text{or} \\ V_{NC} = 2.2 \text{ V}, 0.5 \text{ V}, \\ V_{NO} \text{ and } V_{COM} = \text{Open}, \end{array} $	Switch ON, See Figure 16	Full	2.75 V	-20		20	nA
		$V_{COM} = 0.5 V,$		25°C		-10	2	10	
COM ON leakage current	I <sub>COM(ON)</sub>	$\label{eq:VNC} \begin{array}{l} V_{NO} \text{ and } V_{NC} = \text{Open}, \\ \text{or} \\ V_{COM} = 2.2 \text{ V}, \\ V_{NO} \text{ and } V_{NC} = \text{Open}, \end{array}$	Switch ON, See Figure 16	Full	2.75 V	-20		20	nA
Digital Control Input (	(IN) <sup>(2)</sup>								
Input logic high	V <sub>IH</sub>	V <sub>IO</sub> = 1.65 V to 1.95 V		Full		0.65 × V <sub>IO</sub>		V <sub>IO</sub>	V
Input logic low	V <sub>IL</sub>	V <sub>IO</sub> = 1.65 V to 1.95 V		Full		0		0.35 × V <sub>IO</sub>	V
Input leakage current	I <sub>IH</sub> , I <sub>IL</sub>	$V_{I} = V_{IO} \text{ or } 0$		25°C Full	2.75 V	-2 -20		2 20	nA

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

 (2) All unused digital inputs of the device must be held at V<sub>IO</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

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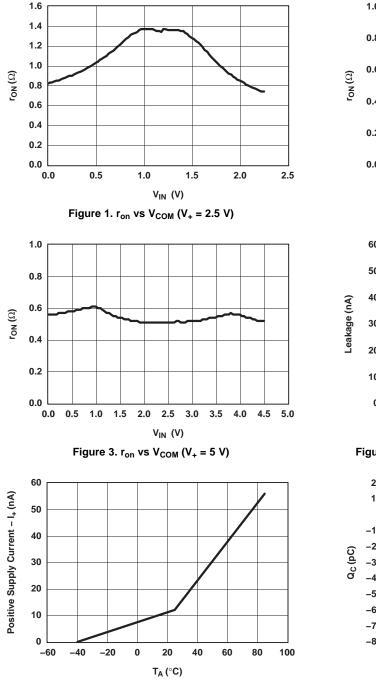
## ELECTRICAL CHARACTERISTICS FOR 2.5-V SUPPLY <sup>(1)</sup> (continued)

 $V_{+} = 2.25$  V to 2.75 V,  $V_{IO} = 1.65$  V to 1.95 V,  $T_{A} = -40^{\circ}$ C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONI	DITIONS	T <sub>A</sub>	V.	MIN	TYP	MAX	UNIT
Dynamic	1		<b>I</b>		L				
Turn-on time	t <sub>ON</sub>	$V_{COM} = V_+,$	C <sub>L</sub> = 35 pF,	25°C	2.5 V	5	20	35	ns
	ON	$R_L = 50 \Omega$ ,	See Figure 18	Full	2.25 V	5		40	110
Turn-off time	town	$V_{COM} = V_+,$	C <sub>L</sub> = 35 pF,	25°C	2.5 V	2	10	20	ns
rum-on time	t <sub>OFF</sub>	$R_L = 50 \Omega$ ,	See Figure 18	Full	2.25 V	2		25	115
Break-before-make	taav	$V_{\rm NC} = V_{\rm NO} = V_{\rm +}/2,$	C <sub>L</sub> = 35 pF,	25°C	2.5 V	1	11	20	ns
time	t <sub>BBM</sub>	$R_L = 50 \Omega$ ,	See Figure 19	Full	2.25 V	1		25	113
Charge injection	Q <sub>C</sub>	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C <sub>L</sub> = 1 nF, See Figure 23	25°C	2.5 V		5		рС
NO OFF capacitance	C <sub>NO(OFF)</sub>	$V_{NO} = V_+ \text{ or GND},$ Switch OFF,	See Figure 17	25°C	2.5 V		38		pF
NC, NO ON capacitance	C <sub>NC(ON)</sub> , C <sub>NO(ON)</sub>	$V_{NC}$ or $V_{NO} = V_{+}$ or GND, Switch ON,	See Figure 17	25°C	2.5 V		135		pF
COM ON capacitance	C <sub>COM(ON)</sub>	$V_{COM} = V_+ \text{ or GND},$ Switch ON,	See Figure 17	25°C	2.5 V		135		pF
Digital input capacitance	CI	$V_I = V_{IO}$ or GND,	See Figure 17	25°C	2.5 V		6.5		pF
Bandwidth	BW	$R_{L} = 50 \Omega$ , Switch ON,	See Figure 20	25°C	2.5 V		40		MHz
OFF isolation	O <sub>ISO</sub>	$\begin{array}{l} R_{L}=50\ \Omega,\\ f=1\ MHz, \end{array}$	See Figure 21	25°C	2.5 V		-63		dB
Crosstalk	X <sub>TALK</sub>	$\begin{array}{l} R_{L}=50\ \Omega,\\ f=1\ MHz, \end{array}$	See Figure 22	25°C	2.5 V		-63		dB
Total harmonic distortion	THD	$R_L = 600 \Omega,$ $C_L = 50 pF,$	f = 20 Hz to 20 kHz, See Figure 24	25°C	2.5 V		0.00 8		%
Supply									
Positive supply		$V_{I} = V_{IO}$ or GND		25°C	2.75 V		10	25	5 nA
current	I+			Full				100	ПА

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## **TYPICAL PERFORMANCE**





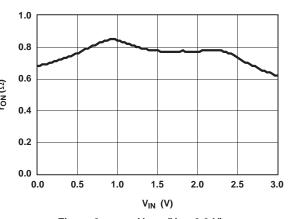


Figure 2.  $r_{on}$  vs V<sub>COM</sub> (V<sub>+</sub> = 3.3 V)

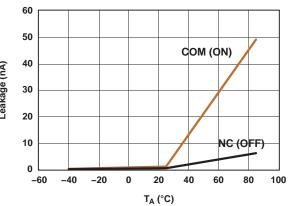


Figure 4. Leakage Current vs Temperature (V<sub>+</sub> = 5 V)

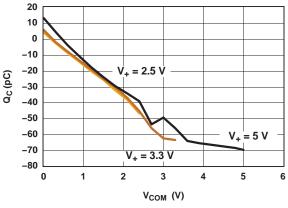
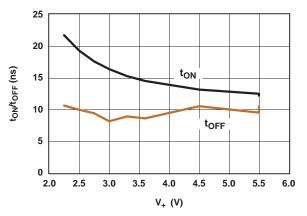
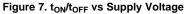


Figure 6. Charge Injection ( $Q_C$ ) vs  $V_{COM}$ 



**TYPICAL PERFORMANCE (continued)** 





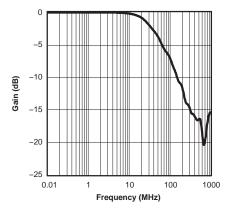


Figure 9. Gain vs Frequency (V<sub>+</sub> = 5 V)

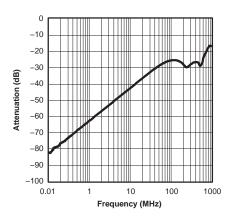


Figure 11. OFF Isolation vs Frequency ( $V_{+} = 5 V$ )

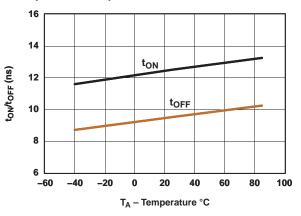


Figure 8.  $t_{ON}/t_{OFF}$  vs Temperature (V<sub>+</sub> = 5 V)

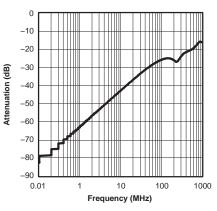


Figure 10. Crosstalk vs Frequency (V<sub>+</sub> = 5 V)

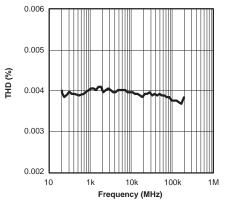
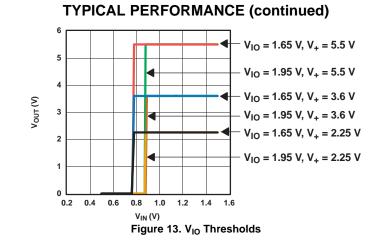


Figure 12. Total Harmonic Distortion vs Frequency  $(V_{+} = 2.5 V)$ 







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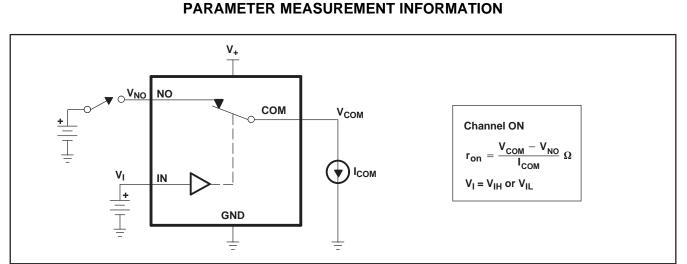


Figure 14. ON-State Resistance (ron)

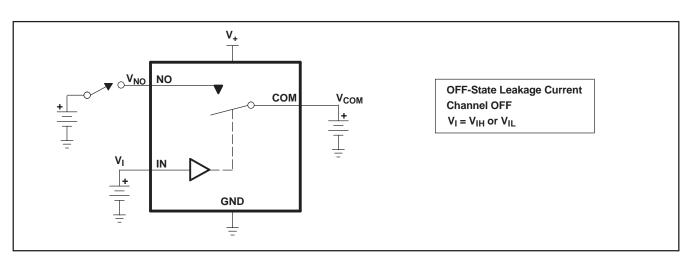


Figure 15. OFF-State Leakage Current (I<sub>COM(OFF)</sub>, I<sub>NC(OFF)</sub>, I<sub>COM(PWROFF)</sub>, I<sub>NC(PWR(FF)</sub>)

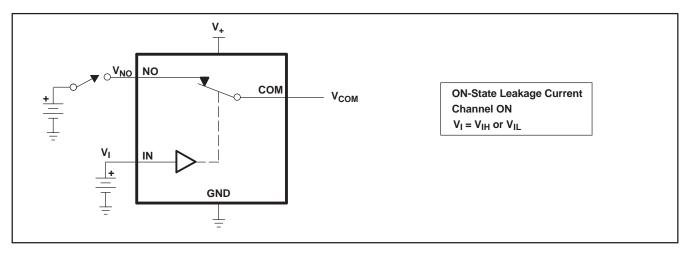


Figure 16. ON-State Leakage Current (I<sub>COM(ON)</sub>, I<sub>NC(ON)</sub>)

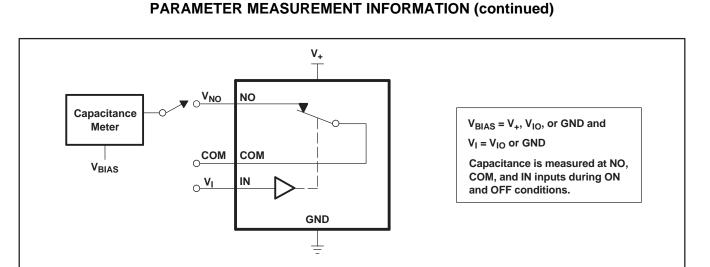
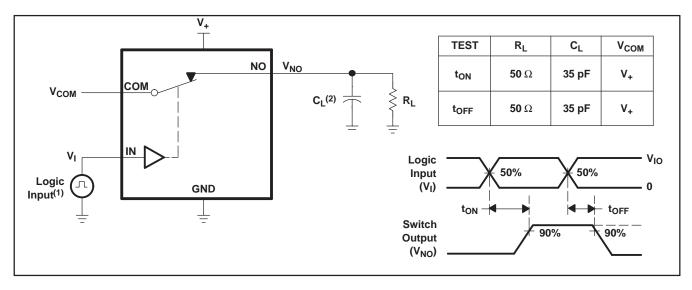


Figure 17. Capacitance (C<sub>I</sub>,  $C_{COM(OFF)}$ ,  $C_{COM(ON)}$ ,  $C_{NC(OFF)}$ ,  $C_{NC(ON)}$ )



<sup>(1)</sup> All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>r</sub> < 5 ns, t<sub>f</sub> < 5 ns. <sup>(2)</sup> C<sub>L</sub> includes probe and jig capacitance.

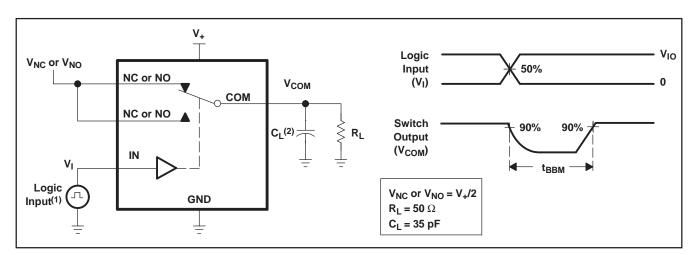
### Figure 18. Turn-On (t<sub>ON</sub>) and Turn-Off Time (t<sub>OFF</sub>)

**FEXAS** 



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<sup>(1)</sup> All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>r</sub> < 5 ns, t<sub>f</sub> < 5 ns. <sup>(2)</sup> C<sub>L</sub> includes probe and jig capacitance.

Figure 19. Break-Before-Make Time (t<sub>BBM</sub>)

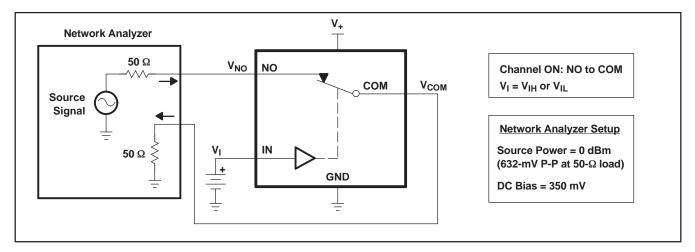
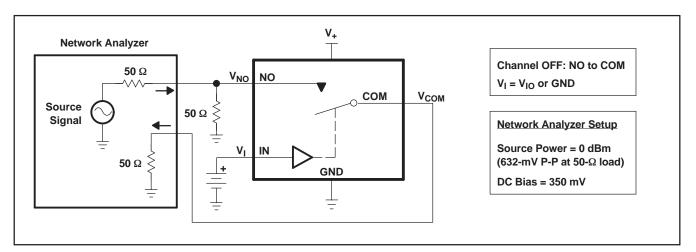


Figure 20. Bandwidth (BW)









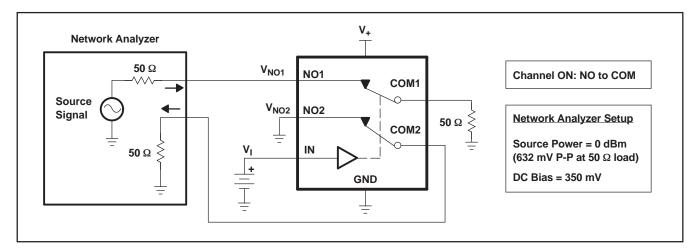
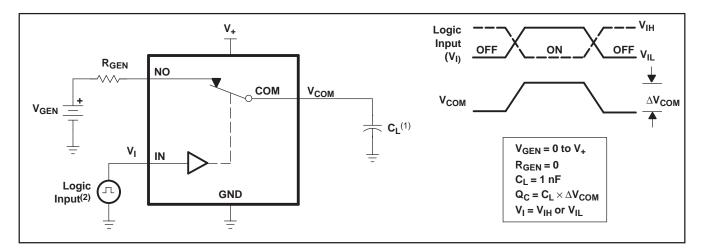


Figure 22. Crosstalk (X<sub>TALK</sub>)



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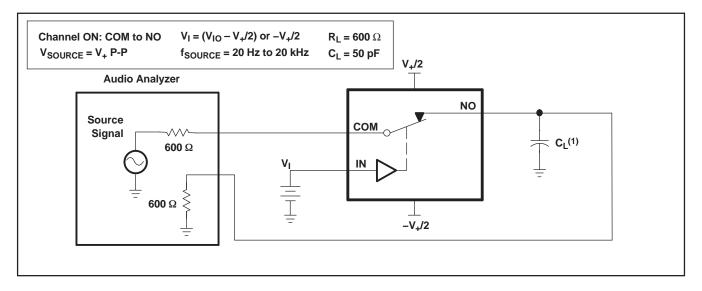
### PARAMETER MEASUREMENT INFORMATION (continued)



 $^{(1)}\,$  CL includes probe and jig capacitance.

<sup>(2)</sup> All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>f</sub> < 5 ns, t<sub>f</sub> < 5 ns.

#### Figure 23. Charge Injection (Q<sub>C</sub>)



 $^{(1)}\,$  CL includes probe and jig capacitance.

#### Figure 24. Total Harmonic Distortion (THD)



## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	e Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A6542YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	JHN	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <= 1000ppm threshold. Antimony trioxide based flame retardants must also meet the <= 1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(<sup>6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## PACKAGE MATERIALS INFORMATION

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Texas Instruments

## TAPE AND REEL INFORMATION





## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions	are	nominal
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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A6542YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

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## PACKAGE MATERIALS INFORMATION

18-Jan-2020



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A6542YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

# YZP0008



## **PACKAGE OUTLINE**

## DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



# YZP0008

# **EXAMPLE BOARD LAYOUT**

## DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



# YZP0008

# **EXAMPLE STENCIL DESIGN**

## DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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